

Journal of Nuclear Materials 297 (2001) 69-76



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# An ab initio study on formation and desorption reactions of H<sub>2</sub>O molecules from surface hydroxyl groups in silicates

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Received 23 October 2000; accepted 8 April 2001

#### Abstract

Effects of the Al atom on the formation and desorption reactions of  $H_2O$  molecules from surface hydroxyl groups in silicates have been investigated by ab initio molecular calculations for  $Si(OH)_4$  and  $(HO)_3Si(OH)Al(OH)_3$  cluster models. The analysis of the potential energy profiles for the reactions of surface hydroxyls shows that the  $H_2O$  complex formation and the  $H_2O$  desorption through the interaction of the surface hydroxyls with  $Al(OH)_3$  units yield relatively low activation energies. The low energies of these reactions are closely connected with the changes of geometrical parameters and charge distributions caused by the interaction of the surface hydroxyls with  $Al(OH)_3$  units. © 2001 Elsevier Science B.V. All rights reserved.

PACS: 82.65.M; 31.15.A; 71.15.F; 68.35.B

### 1. Introduction

Tritium release is an important performance of ceramic tritum breeding materials such as lithium silicate and lithium titanate in a fusion reactor. Some improvements of these materials have been done to enhance the low-temperature tritium release [1,2]. The tritium generated by the  $^6\text{Li}(n,\alpha)^3\text{H}$  reactions mainly exist as hydroxyls on the surface of breeding materials [3,4]. The surface hydroxyls play an important role in the tritium release behavior from the solid breeder materials.

Addition of other elements, such as Al, Mg, etc., to the breeding materials is one of several factors influencing the properties of the surface hydroxyls [1,2]. Addition of Al atoms to the lithium silicate improves the tritium release performance at low temperatures. We have investigated the influence of trivalent elements, such as B, Al, and Ga, on the properties of surface hy-

droxyls in lithium silicate by ab initio molecular orbital calculations [5,6]. It has been confirmed that the interaction of the trivalent elements with the surface hydroxyls increases the ionicity of surface hydrogen, and decreases the deprotonation energy. Especially, the direct interaction of Al atom with the surface hydroxyl induces the largest ionicity of surface hydrogen among B, Al, and Ga atoms.

The aim of the present study is to investigate the effect of the Al atoms on the formation and desorption reactions of the  $H_2O$  molecules from the geminal surface hydroxyl in silicates.

## 2. Models and methods

# 2.1. Models

Fig. 1 shows local surface structures of silicate glasses that are formed in pure and Al-doped lithium silicates with the sudden changes caused due to an irradiation and a rapid cooling [7–9]. The Si(OH)<sub>4</sub> cluster model represents the local structure of silicate glass formed in silicate. The (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> cluster model is used to simulate the effect of Al atom doped in silicate glass.

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Fig. 1. Structural schemes of geminal surface hydroxyl groups in: (a) silicate glass; (b) silicate glass containing A1 atom.

The Si(OH)<sub>4</sub> molecule has been considered as a model for both isolated and geminal types of surface hydroxyls in silica [10,11]. The (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> molecule has been used for understanding the chemical property of hydroxyl on aluminosilicate mineral [12].

In the cluster models, H<sub>s</sub> and O<sub>s</sub> represent the surface hydrogen and oxygen atoms, respectively. Other hydrogen atoms, called 'terminators', in the cluster models are used to saturate the dangling bonds of 'surface' oxygen atoms. It has been shown that such hydrogen terminators do not substantially affect the nature of the Si–O bond [13]. The oxygen atoms terminated by hydrogens can be considered as the bridging oxygen atoms.

# 2.2. Calculation methods

The Gaussian 94 program [14] is used to carry out all ab initio calculations presented here. The theoretical calculations are based on ab initio molecular orbital theory using Hartree–Fock and Møller–Plesset perturbation theories [15,16]. The electron correlation corrections are limited to the MP2 level. The MP2 method has been shown to account for typically 85–95% of the correlation energy in reasonable computational time [17]. The basis sets used here are the standard 6-31G\*\* basis sets implemented in the Gaussian 94 program, which have p- and d-type polarization functions for the hydrogen and heavy atoms (Si, Al and O), respectively.

All geometrical parameters are fully optimized without assuming symmetry on the structure. The vibrational frequencies are calculated using analytical second derivatives of the total energy. The transition states reported here are confirmed to have one imaginary frequency. The unscaled frequencies are used in the calculations for the vibrational zero-point energy (ZPE) correction. The intrinsic reaction coordinates (IRC) are calculated in order to check and obtain energy profiles

of the reactions discussed here [18,19]. The natural atomic charges are computed using the natural bond orbital (NBO) analysis [20–23].

#### 3. Results and discussions

#### 3.1. Geometrices

The formation and desorption of an H<sub>2</sub>O molecule geminal surface hydroxyl from the groups (-O<sub>1</sub>H<sub>1</sub>, -O<sub>2</sub>H<sub>2</sub>) simulated by the Si(HO)<sub>4</sub> cluster are presented in Fig. 2. The influence of the Al(OH)<sub>3</sub> unit on the formation and desorption of an H<sub>2</sub>O molecule is simulated by the (OH)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> cluster (see Fig. 3). In both the models, the formed H<sub>2</sub>O molecule is adsorbed on the isolated cluster, and takes the form of H<sub>2</sub>O complex at the first stage. Important bond distances and angles of these structures obtained with no constraints at the HF/6-31G\*\* and MP2/6-31G\*\* levels are shown in Tables 1 and 2, respectively. The natural atomic charges on the most significant atoms are also listed in the above tables.

The geometrical parameters calculated for the  $Si(OH)_4$  and  $(HO)_3Si(OH)Al(OH)_3$  clusters as the reactants can be compared to the experimental and theoretical values reported previously. The Si–O bond lengths calculated at the HF and MP2 levels for the  $Si(OH)_4$  reactant cluster are in good agreement with the experimental values of 1.637 Å for cyclohexylsilanetriol  $(C_6H_{11}Si(OH)_3)$  [24] and of 1.67 Å for isolated monosilicate ion  $[SiO_3(OH)_3^-]$  in NaCaSiO<sub>3</sub>(OH) [25]. Our calculated values of Si–O and O–H bond lengths and  $\angle OSiO$  bond angle for the  $Si(OH)_4$  reactant cluster are also in good agreement with the calculations by Kassab [26] at the HF/6-31G level (Si–O = 1.625 Å, O–H = 0.93 Å and  $\angle OSiO = 108.88^\circ$ ). The geometrical parameters

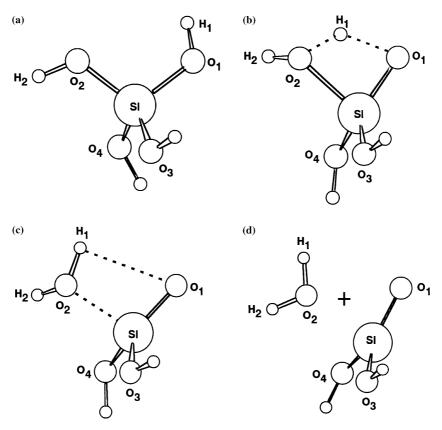


Fig. 2. Optimized structures (MP2/6-31 $G^{**}$ ) and atom labels for the  $H_2O$  formation and desorption reactions from geminal surface hydroxyl in silicate glass: (a) geminal surface hydroxyl; (b) transition state; (c)  $H_2O$  complex; (d)  $H_2O$  and dehydrated clusters. Terminating H atoms are unlabeled.

of the Si(OH)<sub>4</sub> reactant cluster are consistent with previous experimental and theoretical values.

In the Si(OH)Al moiety of (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> reactant cluster, the geometrical parameters calculated here are slightly different from the experimental and theoretical values reported previously for structural information of aluminosilicates [27,28]. The average experimental Si-O and Al-O bond lengths and ∠SiOAl bond angle of pyrope crystal (Mg<sub>3</sub>Al<sub>2</sub>Si<sub>3</sub>O<sub>12</sub>) are 1.635 A, 1.886 A and 130.0°, respectively [27]. The corresponding values have been calculated to be 1.66 Å, 1.98 A and 133.5°, respectively, in the previous theoretical study [28] wherein the cluster structure is constrained to the C<sub>s</sub> group. The ∠SiOAl bond angle in the (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> reactant cluster optimized here is about 30° smaller than the above experimental and theoretical values of the ∠SiOAl bond angle. The above average experimental values are for the bulk structure. The imposition of the C<sub>s</sub> symmetry in the geometry optimization makes the bond lengths and angle of the Si(OH)Al moiety in the (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> cluster close to those for the bulk structure. However, the surface structure of aluminosilicates is not always in

agreement with the bulk structure estimated by the experimental techniques such as X-ray diffraction which only give the indirect structural information. On the other hand, an unusually high frequency for the streching vibration  $v_{\rm OH}$  of the bridging OH group in amorphous aluminosilicates was observed in the range 3720–3740 cm<sup>-1</sup> [29]. The high frequency was explained with an unusually small SiOAl angle calculated at 93° by quantum chemical calculations [28], which was very close to the ∠SiOAl bond angle in the (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> reactant cluster optimized in this study. The other geometrical parameters presented here are also consistent with those reported. Thus, the Si(O-H)Al bridge is considered to take the small SiOAl bond angle in the surface structure of aluminosilicates. Also, the oxygen atom  $(O_5)$  of Al $(OH)_3$  unit interacts with the silicon atom by the request of the unusually small SiOAl bond angle.

As stated above, the (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> reactant cluster optimized here without symmetry constraint is considered to represent a surface structure of the Si(OH)Al bridge in aluminosilicates. Moreover, all vibrational frequencies for the (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub>

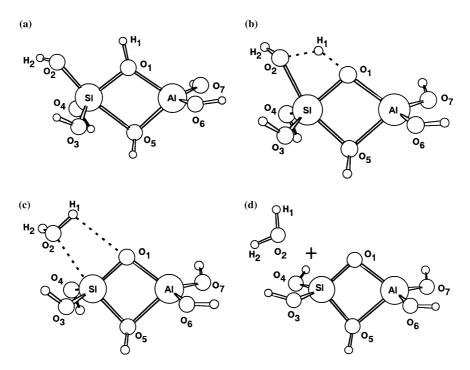


Fig. 3. Optimized structures (MP2/6-31 $G^{**}$ ) and atom labels for the  $H_2O$  formation and desorption reactions from geminal surface hydroxyl in silicate glass containing Al atom: (a) geminal surface hydroxyl interacting with  $Al(OH)_3$  unit; (b) transition state; (c)  $H_2O$  complex; (d)  $H_2O$  and dehydrated clusters. Terminating H atoms are unlabeled.

Table 1 Geometrical parameters and natural charges at  $HF/6-31G^{**}$  and  $MP2/6-31G^{**}$  levels for reactant, transition state,  $H_2O$  complex and products in the  $H_2O$  formation and desorption reactions from geminal surface hydroxyl in silicate glass

	Reactant		TS		H <sub>2</sub> O complex		Products	
	HF	MP2	FH	MP2	HF	MP2	HF	MP2
Parameters								
$d(Si-O_1)$	1.628	1.651	1.549	1.576	1.507	1.541	1.490	1.530
$d(Si-O_2)$	1.628	1.651	1.828	1.887	1.929	1.970	_	_
$d(O_1-H_1)$	0.942	0.962	1.407	1.478	2.446	2.415	_	-
$d(O_2-H_2)$	0.942	0.962	0.947	0.969	0.949	0.970	0.943	0.961
$\angle O_1SiO_2$	106.6	106.0	83.8	84.6	98.8	98.5	-	-
Charges								
q(Si)	2.602	2.599	2.561	2.549	2.513	2.504	2.493	2.477
$q(\mathbf{O}_1)$	-1.180	-1.181	-1.318	-1.312	-1.328	-1.316	-1.243	-1.229
$q(O_2)$	-1.180	-1.181	-1.112	-1.104	-1.002	-1.014	-0.971	-0.974
$q(H_1)$	0.529	0.531	0.602	0.598	0.569	0.572	0.486	0.487
$q(H_2)$	0.529	0.531	0.545	0.548	0.557	0.562	0.486	0.487

Geometrical parameters are given in angstroms and degrees.

cluster optimized here are real. That is to say, the  $(HO)_3Si(OH)Al(OH)_3$  reactant cluster optimized here corresponds to the true local minimum within the model. By contrast, the  $C_s$  symmetry does not provide a true local energy minimum for the  $(HO)_3Si(OH)Al(OH)_3$  reactant cluster though the imposition of the symmetry gives the structural informa-

tion which is correspondent to the bulk structure of aluminosilicates. We confirm that the vibrational analysis yields two imaginary frequencies for the  $C_s$  structure of  $(HO)_3Si(OH)Al(OH)_3$  cluster. Thus, the  $C_s$  symmetry is not taken into the optimization in this study. Our goal is to examine the influence of  $Al(OH)_3$  unit on the  $H_2O$  formation and desorption from geminal surface

Table 2 Geometrical parameters and natural charges at HF/6-31G\*\* and MP2/6-31G\*\* levels for reactant, transition state, H<sub>2</sub>O complex and products in the H<sub>2</sub>O formation and desorption reactions from geminal surface hydroxyl in silicate glass containing Al atom

	Reactant		TS		H <sub>2</sub> O complex		Products	
	HF	MP2	HF	MP2	HF	MP2	HF	MP2
Parameters								
$d(Si-O_1)$	1.745	1.780	1.693	1.726	1.604	1.640	1.590	1.617
$d(Si-O_2)$	1.669	1.694	1.854	1.868	2.301	2.113	_	_
$d(Al-O_1)$	1.871	1.871	1.809	1.825	1.781	1.807	1.780	1.810
$d(O_1-H_1)$	0.944	0.964	1.195	1.202	2.317	2.135	_	_
$d(O_2-H_2)$	0.942	0.963	0.945	0.973	0.946	0.969	0.943	0.961
$\angle O_1SiO_2$	92.7	91.6	75.9	76.2	82.6	83.8	_	_
$\angle SiO_1Al$	107.2	105.5	102.5	101.1	101.2	99.3	101.3	99.1
Charges								
q(Si)	2.627	2.625	2.612	2.609	2.615	2.600	2.602	2.597
q(Al)	2.151	2.152	2.160	2.160	2.145	2.140	2.151	2.148
$q(O_1)$	-1.215	-1.227	-1.367	-1.366	-1.402	-1.401	-1.380	-1.374
$q(\mathbf{O}_2)$	-1.209	-1.210	-1.149	-1.155	-1.007	-1.022	-0.971	-0.974
$q(H_1)$	0.569	0.576	0.622	0.625	0.538	0.561	0.486	0.487
$q(\mathrm{H}_2)$	0.521	0.522	0.534	0.538	0.530	0.551	0.486	0.487

Geometrical parameters are given in Ångstroms and degrees.

hydroxyl, but not to resolve detailed structure of bulk equilibrium geometries. Therefore, we adopt the C<sub>1</sub> structure of (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> cluster as the reactant in this study. All C<sub>1</sub> structures of clusters computed as reactant, H<sub>2</sub>O complex and product models are confirmed to be true local minima.

## 3.2. Electron correlation effects on structures

The inclusion of electron correlation energy with the MP2 calculation give virtually the same bond lengths and angles as the HF calculation (Tables 1 and 2) in most cases. However, detailed observations of the geometrical parameters show that the MP2 structures have characteristic differences compared with the HF structures with respect to the intermolecular bond distances of the H<sub>2</sub>O complexes. Most of intramolecular bond distances become longer by including electron correlation [30], while the intermolecular O<sub>1</sub>-H<sub>1</sub> bond distances, which are only observed in the H<sub>2</sub>O complexes, become somewhat shorter. The intermolecular Si-O2 bond distance in the H<sub>2</sub>O complex of the Si(OH)<sub>4</sub> cluster is lengthened by the inclusion of electron correlation. On the contrary, the electron correlation yields shorter intermolecular Si-O<sub>2</sub> bond distance in the H<sub>2</sub>O complex of (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> cluster.

The inclusion of electron correlation energy yields changes of bond distances as stated above. The lengthening of intramolecular bond distances due to the electron correlation effect is caused by a redistribution of electron density away from bond centers toward the exterior of molecules [30]. The intermolecular  $O_1$ – $H_1$  bond distances are curtailed by the in-

clusion of electron correlation because the correlation yields a stronger interaction by accounting for dispersion effects between the adsorbed  $H_2O$  molecule and the isolated cluster model [31]. The change of intermolecular  $O_1$ – $H_1$  bond distance is caused by the mechanism different from that of intramolecular bond distance.

The intermolecular Si-O<sub>2</sub> bond distances in H<sub>2</sub>O complexes of (HO)3Si(OH)Al(OH)3 cluster, in contrast to the case of the H<sub>2</sub>O complex of Si(OH)<sub>4</sub> cluster, are shortened by the effect of electron correlation. The reason for the shortening of the intermolecular Si-O<sub>2</sub> bond distance is similar to that of the intermolecular O<sub>1</sub>-H<sub>1</sub> bond distances in the H<sub>2</sub>O complexes. Thus, the different mechanisms are considered to be responsible for the changes of the intermolecular Si-O2 bond distances in H<sub>2</sub>O complexes of (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> and Si(OH)<sub>4</sub> clusters. That is to say, it is expected that the redistribution of electron density has a larger effect on the Si-O<sub>2</sub> bond in the H<sub>2</sub>O complex of Si(OH)<sub>4</sub> cluster than on the Si-O<sub>2</sub> bond in the H<sub>2</sub>O complex of (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> cluster. For the Si-O<sub>2</sub> bond in the H<sub>2</sub>O complex of (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> cluster, the effect of dispersion energy is considered to be superior to that of redistribution of electron density.

#### 3.3. Reaction profiles

Fig. 4 shows the MP2/6-31 $G^{**}$  potential energy profiles which correspond to the  $H_2O$  formation and desorption reactions from geminal surface hydroxyls in  $Si(OH)_4$  and  $(HO)_3Si(OH)Al(OH)_3$  clusters. The values in parentheses are the energies calculated at the HF/6-

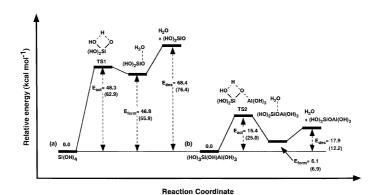


Fig. 4. MP2/6-31 $G^{**}$  reaction profiles for the  $H_2O$  formation and desorption reactions from geminal surface hydroxyls in: (a) silicate glass; (b) silicate glass containing Al atom. The values in parentheses are calculated at HF/6-31 $G^{**}$  level.  $E_{act}$  stands for the activation energy,  $E_{form}$  the formation energy, and  $E_{des}$  the desorption energy.

31G\*\* level. The energies calculated at the MP2 level have larger negative values than those at the HF level because of the electron correlation energy included by MP2 calculation.

The activation energies calculated for the formation of H<sub>2</sub>O molecules in Si(OH)<sub>4</sub> and (HO)<sub>3</sub>Si(OH) Al(OH)<sub>3</sub> clusters are 48.3 (62.9) and 15.4 (25.0) kcal/ mol, respectively. The H<sub>2</sub>O molecules are adsorbed on the isolated clusters to form the H<sub>2</sub>O complexes. The formation energies of H2O complexes in Si(OH)4 and (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> clusters are 46.8 (55.9) and 6.1 (6.9) kcal/mol, respectively. The desorption energies of H<sub>2</sub>O molecules from the H<sub>2</sub>O complexes are 21.6 (20.5) and 11.8 (5.3) kcal/mol, respectively. The desorption energies are calculated as a difference between the sum of the total energies of the H<sub>2</sub>O molecule and isolated cluster, and the total energy of the H<sub>2</sub>O complex. The reaction energies of the formation and desorption of H<sub>2</sub>O molecule in the Si(OH)<sub>4</sub> cluster are decreased by the influence of Al(OH), unit. The lowering in the activation, H<sub>2</sub>O complex formation and H<sub>2</sub>O desorption energies due to the interaction are 32.9 (37.9), 40.7 (49.0) and 9.8 (15.2) kcal/mol, respectively. Such energy lowering is related to the influence of the Al(OH)<sub>3</sub> unit on the geometrical parameters and charge distributions in the reactants, transition states and H<sub>2</sub>O complexes.

At the MP2 level, the  $\angle O_1SiO_2$  bond angle in the  $Si(OH)_4$  reactant cluster decreases from  $106.0^\circ$  to  $91.6^\circ$  by interaction with the  $Al(OH)_3$  unit. The decrease of the  $\angle O_1SiO_2$  bond angle causes a shortening of the  $O_1\cdots O_2$  distance. The shortening of the  $O_1\cdots O_2$  distance due to the interaction is also observed in the calculations at the HF level. Thus, the interaction results in a small displacement in the  $H_1$  hydrogen migration to form  $H_2O$  molecule.

The Al(OH)<sub>3</sub> unit interaction also affects the location of transition state on the reaction coordinate for the hydrogen migration. The geometry of transition state

(TS1) structure in the Si(OH)<sub>4</sub> cluster is also changed by the interaction with the Al(OH)<sub>3</sub> unit. The O<sub>1</sub>-H<sub>1</sub> bond distance and  $\angle O_1SiO_2$  bond angle in TS1 structure are decreased by the interaction. The scrutiny of the relationships of the geometries, the energies and other properties of TS structures to the overall reaction thermochemistry was carried out using the ab initio molecular orbital calculations [32,33]. The TS1 structure with long O<sub>1</sub>-H<sub>1</sub> bond distance is characterized as the late transition state with product-like structure [34,35]. The (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> transition state (TS2) structure with short O<sub>1</sub>-H<sub>1</sub> bond distance is characterized as the early transition state with reactant-like structure [34,35]. The transition state structures are normally characterized by weak partial bonds, that is, those being broken or formed. A linear relation between the calculated distances of bonds being broken in the transition state structures and the calculated heats of reaction has been found [32,33]. The shorter the distances of bonds being broken in the transition state structures, the smaller the energies of reactions. It is consistent with the above findings in [32,33] that the activation and H<sub>2</sub>O complex formation energies calculated for the (HO)<sub>3</sub> Si(OH)Al(OH)<sub>3</sub> cluster are smaller than that for the  $Si(OH)_{4}$  one.

The energy of the  $H_2O$  desorption is substantially depressed by the  $Al(OH)_3$  unit interaction. The desorption energies of  $H_2O$  molecules from the  $H_2O$  complexes are 21.6 (20.5) and 11.8 (5.3) kcal/mol for the  $Si(OH)_4$  and  $(HO)_3Si(OH)Al(OH)_3$  clusters, respectively. The decrease in the desorption energies due to the interaction in  $Al(OH)_3$  unit corresponds to the weaker interaction of  $H_2O$  molecules in the  $H_2O$  complexes.

The  $H_2O$  complexes are found to be stabilized by the  $Si-O_2$  coordination rather than by the hydrogen bond between the  $H_1$  and  $O_1$ . The Wiberg bond indices [36] calculated by the NBO analysis indicate that the interaction between oxygen atom,  $O_2$ , and Si atom in the

H<sub>2</sub>O complexes is significant in the desorption process. The Wiberg bond index is indicative of a bond order. At the MP2 level, the Wiberg bond indices of the  $Si \cdots O_1$ and  $O_1 \cdots H_1$  bonds in the  $H_2O$  complex of  $Si(OH)_4$ cluster are 0.216 and 0.007, respectively. In the H<sub>2</sub>O complex of (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> cluster, the bond indices of the  $Si \cdots O_2$  and  $O_1 \cdots H_1$  bonds at the MP2 level are 0.165 and 0.009, respectively. Relative to the values of the bond indices for the  $Si \cdots O_2$  bonds, those of the bond indices for the  $O_1 \cdots H_1$  bonds are extremely small. The value of the bond index for the  $Si \cdots O_2$  bond in the H<sub>2</sub>O complex of Si(OH)<sub>4</sub> cluster is reduced by the interaction with Al(OH)3 unit. The reduction corresponds to that of the desorption energy due to the interaction with Al(OH)<sub>2</sub> unit. It is understood from these bond indices that the desorption energies are closely associated with the  $Si \cdots O_2$  interaction. The relation of the  $Si \cdots O_2$  interaction to the desorption energy can be recognized from bond distances in the H<sub>2</sub>O complexes as well as from the Wiberg bond indices. At the MP2 level, the  $Si \cdots O_2$  distance increases from 1.970 to 2.113 A by the interaction of Al(OH)<sub>3</sub> unit, while the  $O_1 \cdots H_1$ distance decreases from 2.415 to 2.135 Å (see Tables 1 and 2). The same tendencies are observed for the  $Si \cdots O_2$  and  $O_1 \cdots H_1$  distances in the calculations at the HF level. The increase of the  $Si \cdots O_2$  distance agrees well with the lower interaction energy of the H<sub>2</sub>O complex of (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> cluster. On the other hand, the decrease of the  $O_1 \cdots H_1$  distance is inconsistent with that of the desorption energy. If the formed H<sub>2</sub>O molecule is adsorbed to the isolated cluster by the  $O_1 \cdots H_1$  interaction, the desorption energy should become large with the decrease of the  $O_1 \cdots H_1$  distance due to the interaction. However, the desorption energy of H<sub>2</sub>O molecule from the complex is diminished by the interaction. That is to say, the formed H<sub>2</sub>O molecule is not adsorbed to the isolated cluster by the  $O_1 \cdots H_1$ interaction but by the  $Si \cdots O_2$  interaction. Consequently, the desorption energies of H<sub>2</sub>O molecules from complexes are considered to be mainly connected with the interaction between oxygen atom, O2, in the adsorbed H<sub>2</sub>O molecule and Si atom in the isolated cluster. The  $O_1 \cdots H_1$  interaction energies in the  $H_2O$  complexes should be negligibly small.

The interactions with  $Al(OH)_3$  unit have some influences on the charge distributions as well as on the geometries of reactant, transition state, and  $H_2O$  complex structures. The MP2 natural charges of surface hydrogen  $(H_1)$  in the  $Si(OH)_4$  reactant increase from 0.531e to 0.567e by the interaction of  $Al(OH)_3$  unit. Such an increase in the ionicity of hydrogen  $(H_1)$  results in the decrease of deprotonation energy [5,6]. The increase in the ionicity of hydrogen  $(H_1)$  due to the interaction is also maintained for the transition states. The increase in the ionicity of hydrogen  $(H_1)$  is also observed for the reactant and transition state structures at the HF level.

Thus, the maintaining of the higher ionicity of surface hydrogen due to the interaction with Al(OH)<sub>3</sub> unit causes the H<sub>2</sub>O formation with the lower activation energy.

The interaction with Al(OH)3 unit affects reaction mechanisms as well as reaction energies for the H<sub>2</sub>O formation and desorption from geminal surface hydroxyl in Si(OH)<sub>4</sub> reactant cluster. In the H<sub>2</sub>O formation and desorption reactions in Si(OH)<sub>4</sub> cluster, the energy profile presents that the H<sub>2</sub>O desorption energy is larger than the activation energy for the  $H_2O$  formation. This indicates that the overall H<sub>2</sub>O desorption rate is controlled by the second-stage H<sub>2</sub>O desorption process in Si(OH)<sub>4</sub> cluster. On the contrary, the activation energy for the H<sub>2</sub>O formation is shown to be larger than the H<sub>2</sub>O desorption energy in the energy profile calculated for the (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> cluster. The H<sub>2</sub>O formation process is indicated to be dominant for the  $H_2O$ formation and desorption reactions (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> cluster. Thus, the H<sub>2</sub>O desorption and formation reactions are regarded as rate-determining steps of the H<sub>2</sub>O release from the Si(OH)<sub>4</sub> and (HO)<sub>3</sub>Si(OH)Al(OH)<sub>3</sub> clusters, respectively. It is found that the direct interaction with Al(OH)<sub>3</sub> unit to the surface hydroxyl influences not only reaction energies but also mechanisms for the H<sub>2</sub>O formation and desorption reactions.

The reaction energy profiles shown in Fig. 4 are also very useful from the experimental point of view, since the interaction of  $Al(OH)_3$  unit with the surface hydroxyl groups are found to play a significant role in the formation and desorption reactions of  $H_2O$  molecule on the surface of silicates. It is suggested from the energy profiles that the  $H_2O$  formation and desorption reactions should proceed at low temperatures due to the interaction with  $Al(OH)_3$  unit. The results obtained in the present calculations are consistent with the experimental results [1] wherein the doping of the Al atom is shown to promote the tritium release from lithium silicate at low temperatures. The outcomes of this study are very useful for the understanding of the tritium release behavior from the Al-doped lithium silicate.

#### 4. Conclusions

From the ab initio study with the HF/6-31G\*\* and MP2/6-31G\*\* methods on the influence of the  $Al(OH)_3$  unit on the formation and desorption reactions of  $H_2O$  molecules from the geminal surface hydroxyl in silicate glasses, the following conclusions may be drawn.

 Firstly, the activation, H<sub>2</sub>O complex formation and H<sub>2</sub>O desorption energies are found to be reduced by the interaction of Al(OH)<sub>3</sub> unit with the surface hydroxyls. By the interaction with Al(OH)<sub>3</sub> unit, the rate-determining step of the H<sub>2</sub>O formation and desorption reactions in Si(OH)<sub>4</sub> cluster is shifted

- from the  $H_2O$  desorption reaction to the  $H_2O$  formation one. The  $Al(OH)_3$  unit plays a significant role in the formation and desorption reactions of  $H_2O$  molecules from the geminal surface hydroxyl in silicate glasses.
- 2. Secondly, the changes of the geometrical parameters and charge distributions due to the interaction of Al(OH)<sub>3</sub> unit, which are observed for the reactants, transition states and H<sub>2</sub>O complexes, are directly connected with the reduction of the reaction energies in the formation and desorption of H<sub>2</sub>O molecule. The interaction increases the ionicity of surface hydrogen, and decreases the displacement of the displacement of the cluster structure during the H<sub>2</sub>O formation.

The results obtained in the present study are very useful to understand the reactions between surface hydroxyls in silicate glasses in the scope of the fundamental understanding of tritium release mechanism.

#### Acknowledgements

We gratefully acknowledge the interest and the encouragement presented from Dr S. Jitsukawa and Dr A. Iwamoto.

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